

Fast Recovery Silicon Power Diode

Application:

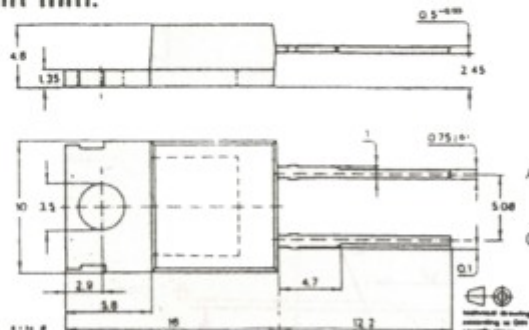
- Fast switched mode power supplies
- Freewheeling diodes and snubber diodes in motor control circuits

Features:

- Multiple diffusion
- Mesa glasspassivated
- Low switch on power losses
- Good soft recovery behavior
- Fast forward recovery time
- Fast reverse recovery time
- Low reverse current
- Very low turn on transient peak voltage
- Very good reverse current stability at high temperature
- Low thermal resistance

BYT 08P /600A /800A

Dimensions in mm:



Cathode connected
with metallic surface

plastic case
DO 220

Absolute maximum ratings

BYT 08P/600 BYT 08P/800

Reverse voltage,			
Repetitive peak reverse voltage	$V_R = V_{RRM}$	600	800 V
Surge forward current			
$t_D = 10$ ms	I_{FSM}	50	A
Repetitive peak forward current	I_{FRM}	16	A
Junction temperature	T_J	150	°C
Storage temperature	T_{sig}	-40... + 150	°C



BYT 08P /600A /800A**Maximum thermal resistances**

Junction case	R_{thJC}	2.0	K/W
Junction ambient	R_{thJA}	85	K/W

Characteristics

		Typ.	Max.
$T_j = 25^\circ\text{C}$, unless otherwise specified			
Forward voltage			
$I_F = 8 \text{ A}$	V_F	1.7	V
$I_F = 8 \text{ A}, T_j = 100^\circ\text{C}$	V_F	1.6	V
Reverse current			
$V_R = V_{RRM}$	I_R	35	μA
$V_R = V_{RRM}, T_j = 100^\circ\text{C}$	I_R	2	mA
Forward recovery time			
$I_F = 8 \text{ A}, di_F/dt \leq 50 \text{ A}/\mu\text{s}$	t_{fr}	350	ns
Turn ON transient peak voltage, Fig.1	V_{FP}	4,5	V
Turn OFF switching characteristic Fig.2			
$I_F = 8 \text{ A}, di_F/dt \leq -32 \text{ A}/\mu\text{s},$			
$V_{Batt} = 200 \text{ V}, T_j = 100^\circ\text{C}$			
Reverse recovery current	I_{RM}	4	A
Reverse recovery time	t_{IRM}	160	ns
$i_R = 0,25 \times I_{RM}$	t_{rr}	100	ns
$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, i_R = 0.25 \text{ A}$	t_{rr}	50	ns



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Turn OFF switching characteristic Fig.2

$I_F = 1 \text{ A}, di_F/dt \leq -50 \text{ A}/\mu\text{s},$

$V_{\text{Batt}} = 200 \text{ V},$

Reverse recovery current	I_{RM}	1.7	A
Reverse recovery time	t_{rr}	75	ns
$I_R = 0,25 \times I_{RM}$			

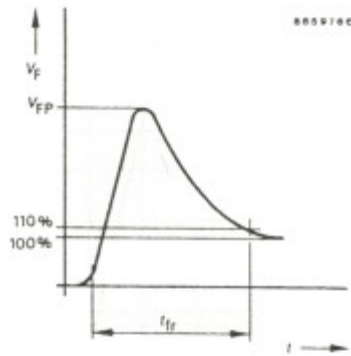


Fig. 1 Turn ON transient peak voltage

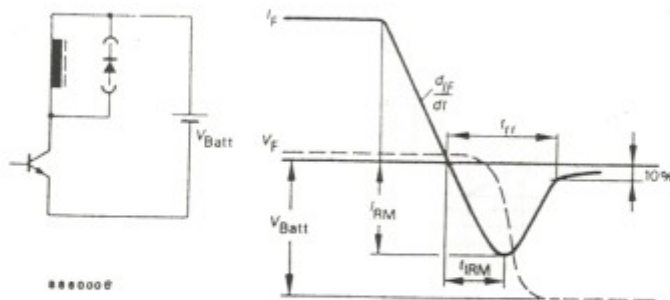
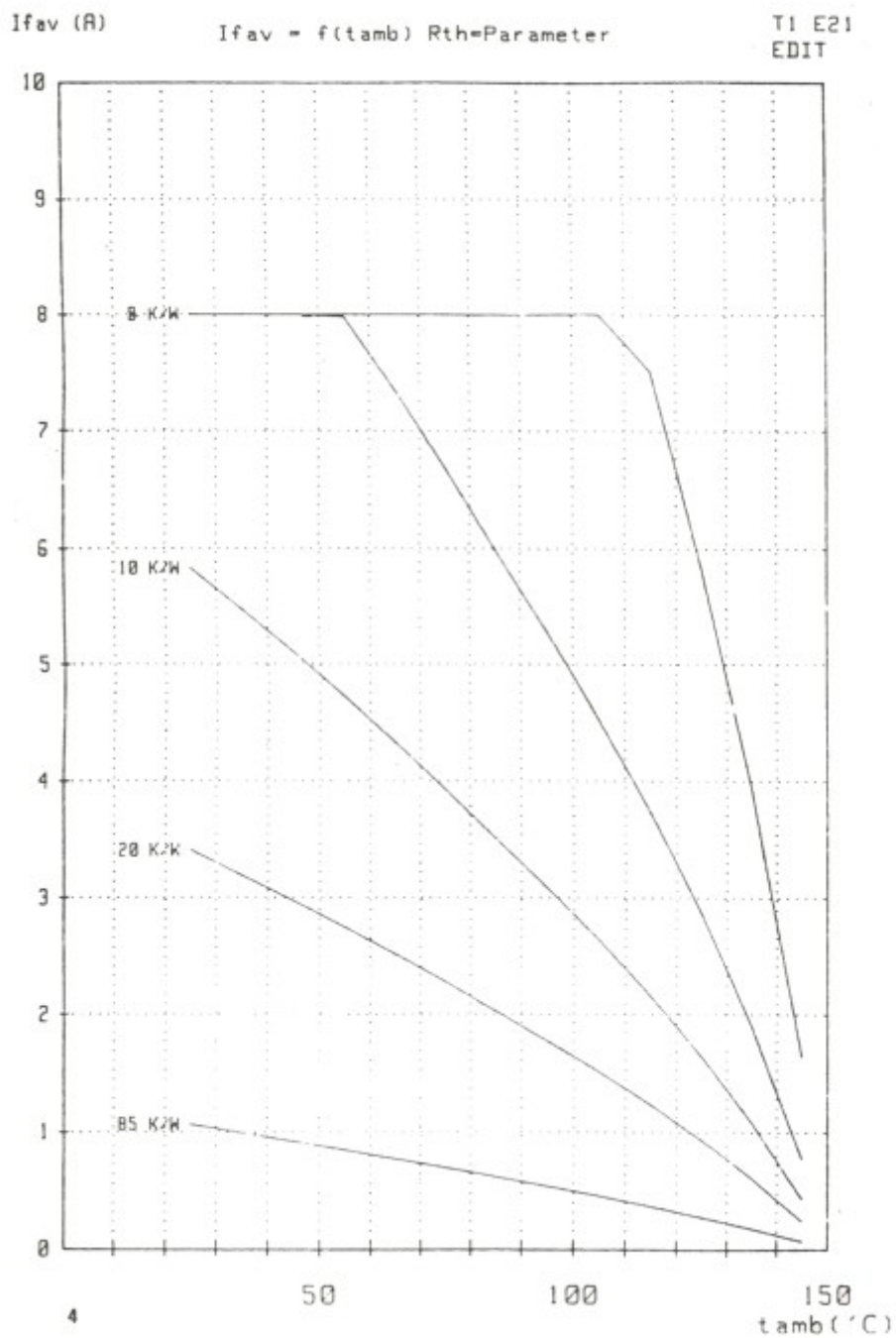


Fig. 2 Test circuit

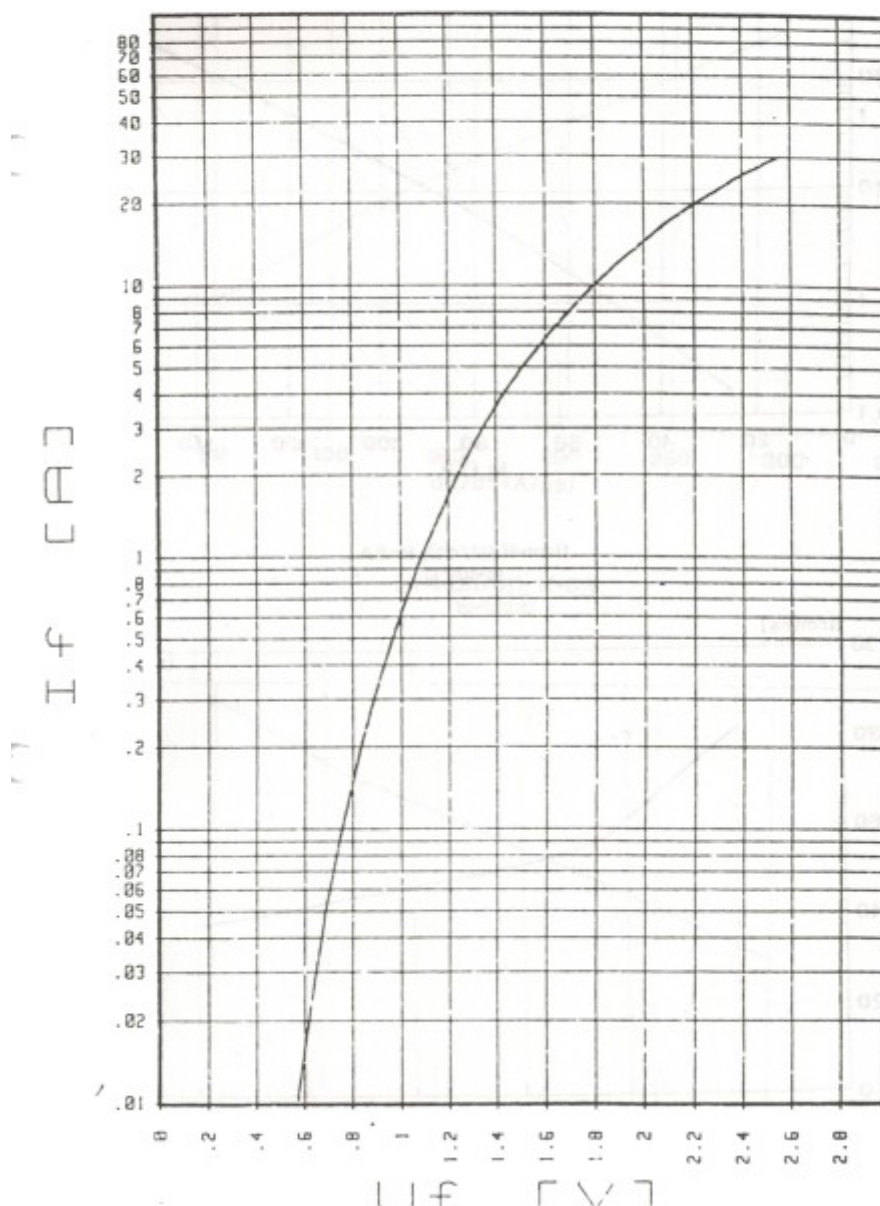


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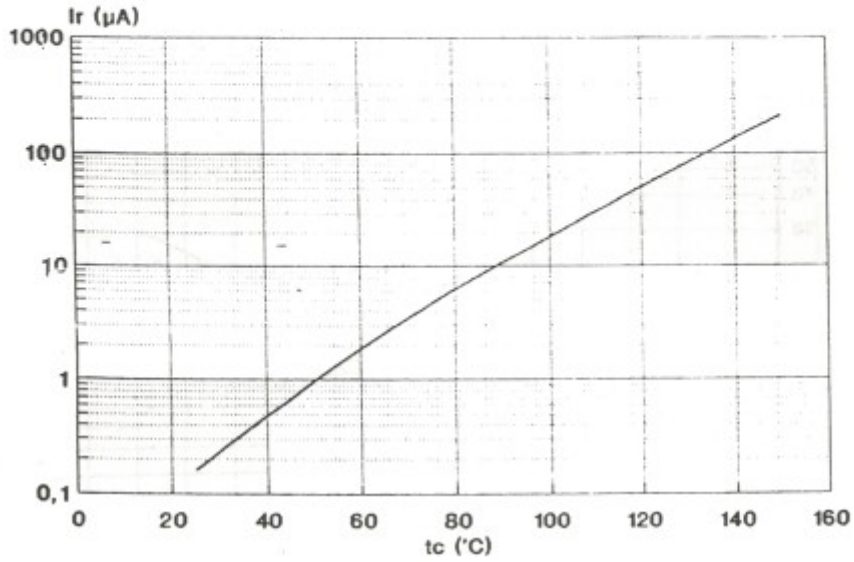
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$$U_f = f(I_f)$$

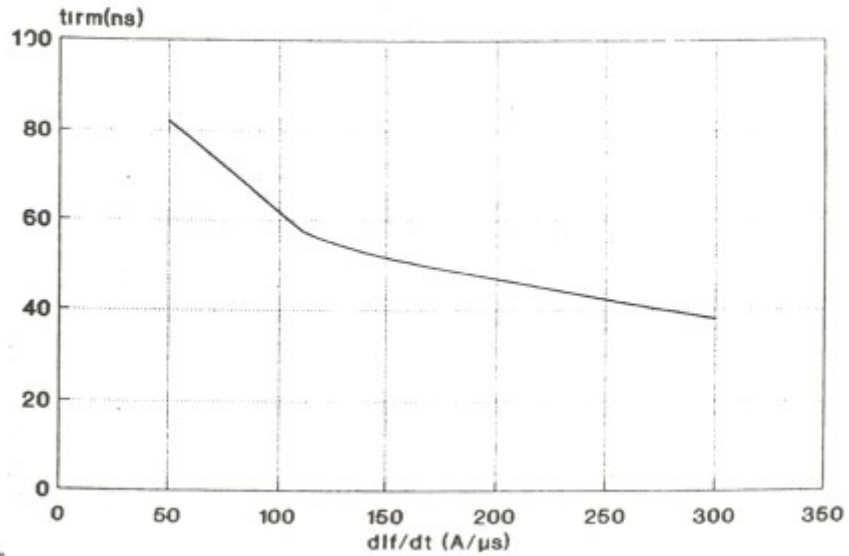


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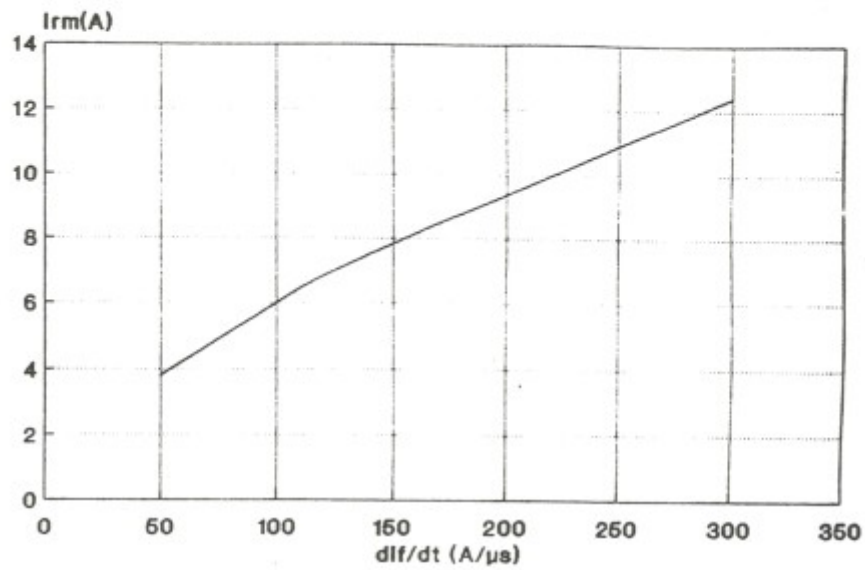
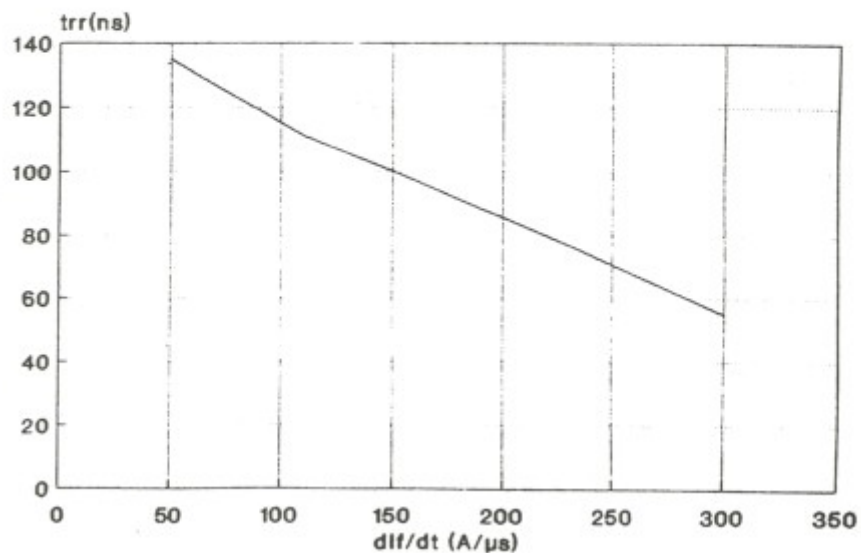
$I_r=f(t_c)$; U_r -Parameter

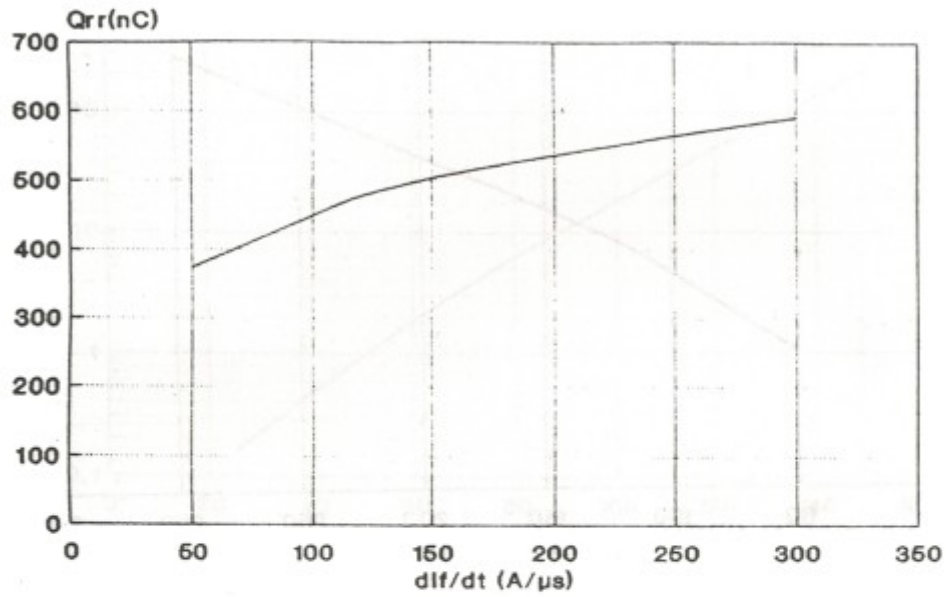


$t_{irm}=f(dI/dt)$; $I_f=8A$
 $t_c=100^\circ C$



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 $I_{rm} = f(dI/dt); I_f = 8A$
 $t_c = 100^\circ C$  $t_{rr} = f(dI/dt); I_f = 8A$
 $t_c = 100^\circ C$ 

BYT 08P /600A /800A $Q_{rr} = f(dI_f/dt); I_f = 8A$
 $t_c = 100^\circ C$ 

We reserve the right to improve technical design
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